



## PRODUCT DATA SHEET



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**Datasheet**



**Resources**



**Samples**

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at [www.jg-semi.cn](http://www.jg-semi.cn). Please email any questions regarding the system integration to [JINGAO\\_questions@jgsemi.com](mailto:JINGAO_questions@jgsemi.com).

### General Description

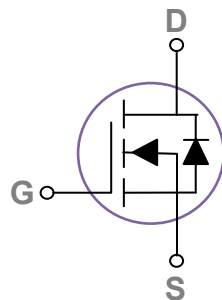
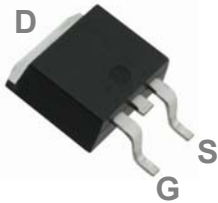
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
60V	24mΩ	30A

### Features

- 60V,30A,  $R_{DS(ON)}=24m\Omega@V_{GS}=10V$
- Improved  $dv/dt$  capability
- Fast switching
- Green Device Available

### TO252 Pin Configuration



### Applications

- Motor Drive
- Power Tools
- LED Lighting

### Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_C=25^\circ\text{C}$ )	30	A
	Drain Current – Continuous ( $T_C=100^\circ\text{C}$ )	16	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	60	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	24	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	22	A
$P_D$	Power Dissipation ( $T_C=25^\circ\text{C}$ )	40	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.32	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-50 to 125	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	3.1	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.07	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	---	24	30	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	28	35	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.0	1.7	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.6	---	mV/°C
gfs	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	---	8	---	S

**Dynamic and switching Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	16.6	24	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	2.2	4.4	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	3.9	8	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A	---	4.6	9	ns
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	14.8	28	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		---	27.2	52	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	7.8	15	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, F=1MHz	---	1180	1720	pF
C <sub>oss</sub>	Output Capacitance		---	68	100	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	45	70	
R <sub>g</sub>	Gate resistance		V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	2.1	

**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	30	A
I <sub>SM</sub>	Pulsed Source Current		---	---	60	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, di/dt=100A/μs	---	17	---	ns
Q <sub>rr</sub>	Reverse Recovery Charge <sup>2</sup>	T <sub>J</sub> =25°C	---	12	---	nC

**Note :**

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=22A, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

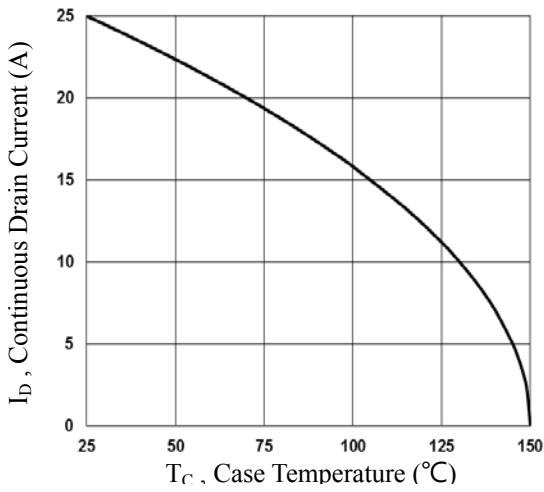


Fig.1 Continuous Drain Current vs.  $T_c$

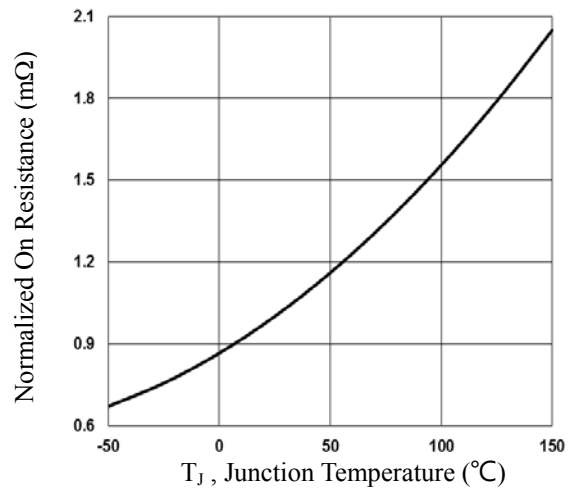


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$

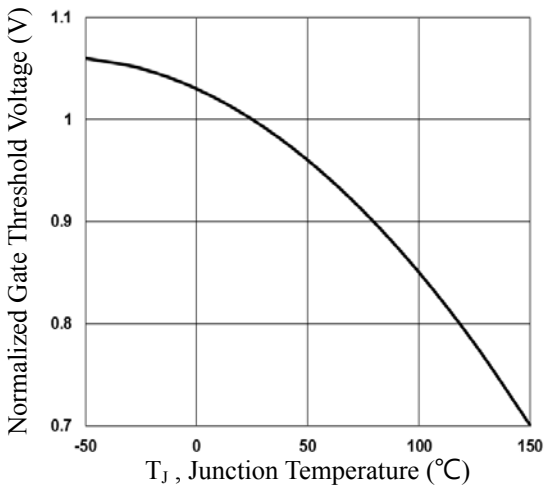


Fig.3 Normalized  $V_{th}$  vs.  $T_j$

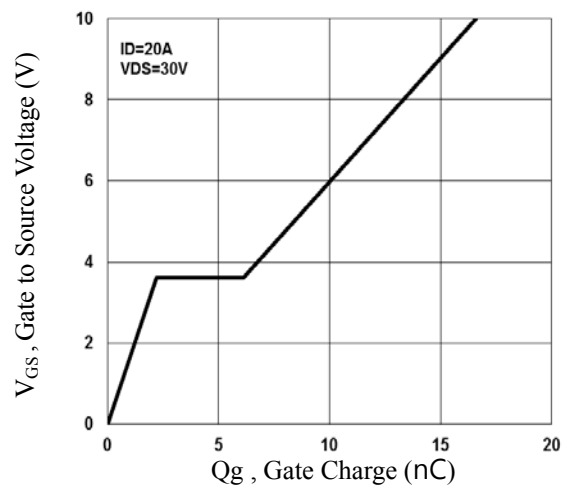


Fig.4 Gate Charge Waveform

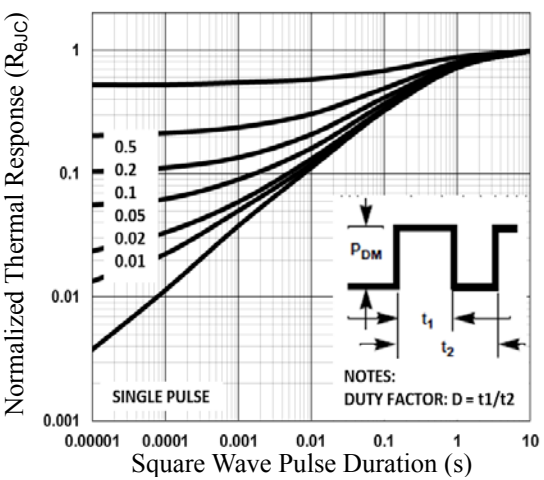


Fig.5 Normalized Transient Impedance

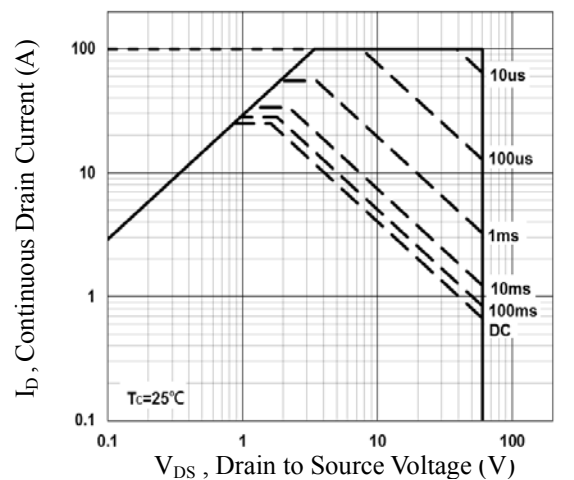
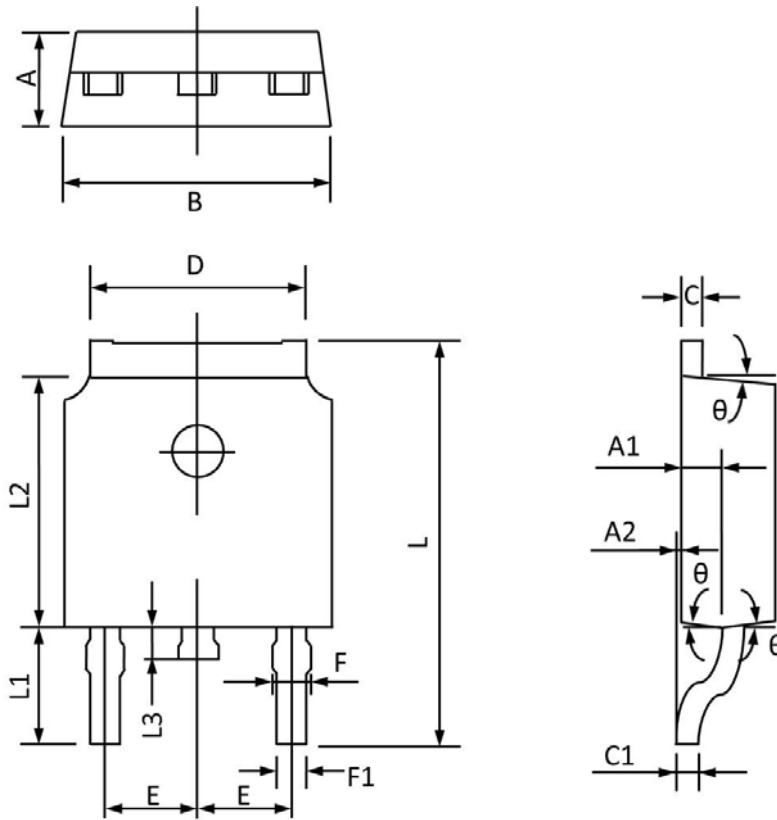


Fig.6 Maximum Safe Operation Area

## TO252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.20	2.40	0.087	0.094
A1	0.91	1.11	0.036	0.044
A2	0.00	0.15	0.000	0.006
B	6.50	6.70	0.256	0.264
C	0.46	0.580	0.018	0.230
C1	0.46	0.580	0.018	0.030
D	5.10	5.46	0.201	0.215
E	2.186	2.386	0.086	0.094
F	0.74	0.94	0.029	0.037
F1	0.660	0.860	0.026	0.034
L	9.80	10.40	0.386	0.409
L1	2.9REF		0.114REF	
L2	6.00	6.20	0.236	0.244
L3	0.60	1.00	0.024	0.039
θ	3°	9°	3°	9°

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